



Si – photodiode with integrated transimpedance amplifier

IQ 800 L
IQ 801 L
IQ 802 L

characteristics:

- Si-photodiode with integrated low noise JFET-amplifier
- integrated feedback resistor and capacitor
- decadic staggered responsivity
- spectral range VIS and NIR
- very low offset- and driftparameters
- high dynamic range
- duale power supply
- hermetically sealed TO-5 package
- assembly isolated to ground
- collimator lense
- components are in conformity with ROHS and WEEE

applications:

- common light-/radiation measuring applications
- detevtor for measuring of low radiation intensities with high signal to noise level
- spectroscopy
- medical diagnostics

maximum ratings:

- operating voltage ± 18 V
- operating temperature range $-25^{\circ}\text{C} \dots +85^{\circ}\text{C}$
- storage temperature range $-40^{\circ}\text{C} \dots +100^{\circ}\text{C}$
- welding temperature (3s) 260°C

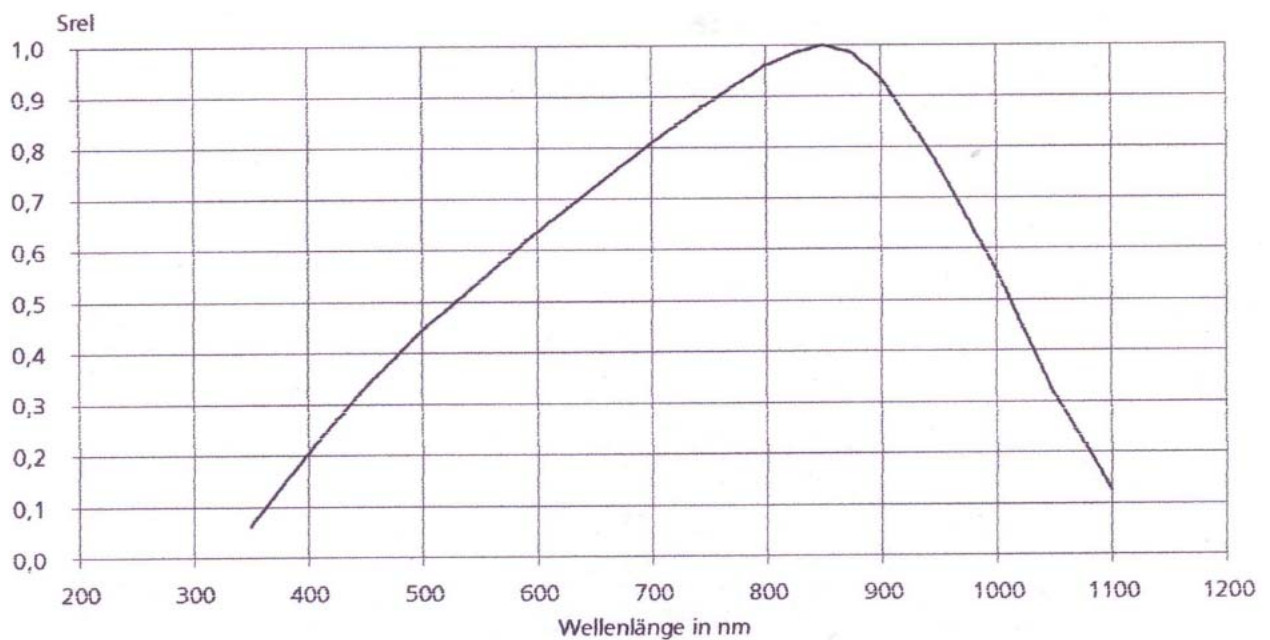


technical data:

common test conditions, as not otherwise specified: $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{V}$
 typ. Data, maximum data in brackets

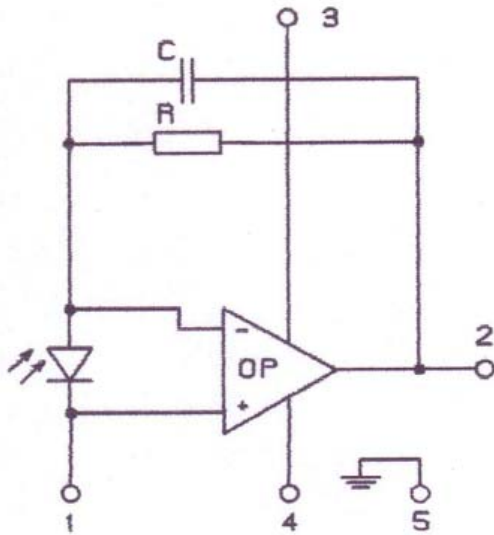
parameter	testcondition	IQ802L	IQ801L	IQ800L	unit
active area		4,8			mm ²
feedback resistor		1	10	100	MΩ
dark offset voltage	$E = 0 \text{ lx}$	$\pm 0,5$	$\pm 0,5$	± 2	mV
noise voltage	$B = 20 \text{ kHz}$	0,2	0,3	0,5	mV _{rms}
spectral range	$S = 0,1 \cdot S_{\text{max}}$	400 ... 1100			nm
max. of spectral responsivity	$S = S_{\text{max}}$	850			nm
max. spectral responsivity	$S = S_{\text{max}}$	0,6	6	60	mV/nW
rise time		3	15	35	μs
bandwidth	-3 dB	120	25	10	kHz
opening angle	$S(\varphi) = 0,5 \cdot S_{\text{max}} \cdot \cos(\varphi)$	± 50			Grad
saturation voltage	$R_L = 2 \text{ k}\Omega$	-14,8 (-14,5)			V
short current		± 45			mA
operation voltage		$\pm 5 \dots \pm 15$			V
current consumption		2,2 (2,6)			mA

relative spectral responsivity



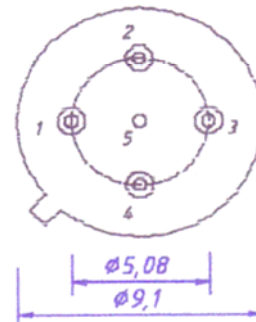
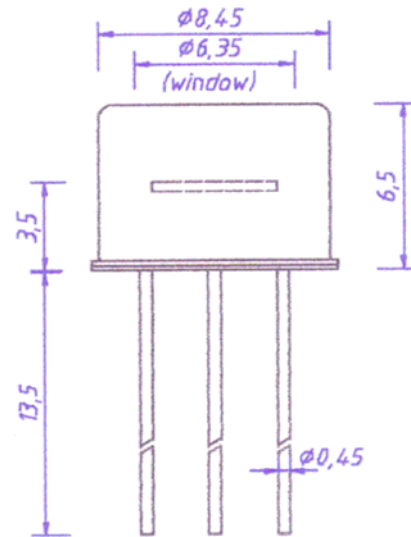


internal circuit



- 1 GND
- 2 Out
- 3 +V_S
- 4 -V_S
- 5 Case

package dimensions



(bottom view)